



YIHUA

PART NAME: BTA08-600C

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Establishment: Carolyn

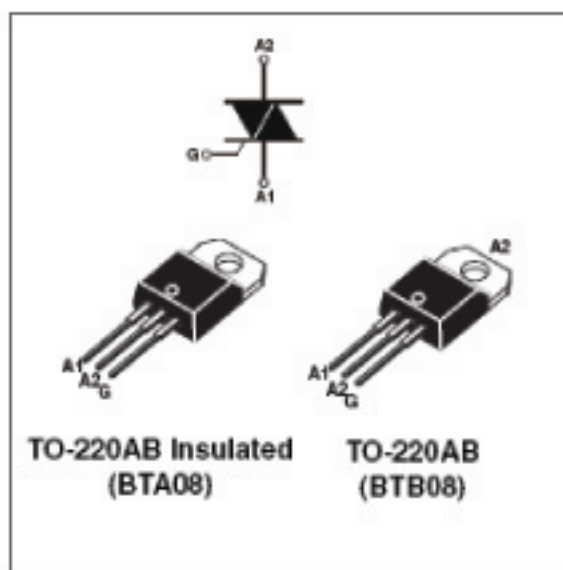
绍兴怡华电子科技有限公司

■ 主要特点:

符号	数值	单位
I_T (RMS)	8	A
V_{DRM}/V_{RRM}	600&800	V
IGT (Q1)	5~50	mA

■ 用途:

BTA/BTB08 双向可控硅系列适用于一般交流开关电路,如:固态继电器,感应马达启动控制,调温控制,调光控制,调速控制...等.



■ 极限值:

符号	参数		数值	单位
$I_{T(RMS)}$	RMS 通态电流	$T_C=90^\circ\text{C}$	8	A
I_{TSM}	通态峰值浪涌电流	$F=50\text{Hz}, t=20\text{ms}$	80	A
I_t	I_t 耗散值	$T_p=10\text{ms}$	36	A^2s
di/dt	通态电流上升值	$F=120\text{Hz}, T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	门极峰值电流	$TP=20\mu\text{s}, T_j=125^\circ\text{C}$	4	A
$P_{G(AV)}$	平均门极耗散功率	$T_j=125^\circ\text{C}$	1	W
T_{stg}	贮存结温范围		-40~+150	$^\circ\text{C}$
T_j	工作结温范围		-40~+125	$^\circ\text{C}$

■ 电特性

■ SNUBBERLESS and Logic Level (3 quadrants)

Symbol	Test Conditions	Quad-rant		T8		BTA08 / BTB08				Unit
				T810	T835	TW	SW	CW	BW	
I_{GT} (1)	$V_D = 12\text{ V}$ $R_L = 30\ \Omega$	I - II - III	MAX.	10	35	5	10	35	50	mA
V_{GT}		I - II - III	MAX.	1.3						V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_j = 125^\circ\text{C}$	I - II - III	MIN.	0.2						V
I_H (2)	$I_T = 100\text{ mA}$		MAX.	15	35	10	15	35	50	mA
I_L	$I_G = 1.2 I_{GT}$	I - III	MAX.	25	50	10	25	50	70	mA
		II		30	60	15	30	60	80	
dV/dt (2)	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	40	400	20	40	400	1000	$\text{V}/\mu\text{s}$
$(dI/dt)_c$ (2)	$(dV/dt)_c = 0.1\text{ V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$		MIN.	5.4	-	3.5	5.4	-	-	A/ms
	$(dV/dt)_c = 10\text{ V}/\mu\text{s}$ $T_j = 125^\circ\text{C}$			2.8	-	1.5	2.98	-	-	
	Without snubber $T_j = 125^\circ\text{C}$			-	4.5	-	-	4.5	7	

■ Standard (4 quadrants)

Symbol	Test Conditions	Quadrant		BTA08 / BTB08		Unit
				C	B	
I_{GT} (1)	$V_D = 12\text{ V}$ $R_L = 30\ \Omega$	I - II - III IV	MAX.	25 50	50 100	mA
V_{GT}		ALL	MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_j = 125^\circ\text{C}$	ALL	MIN.	0.2		V
I_H (2)	$I_T = 500\text{ mA}$		MAX.	25	50	mA
I_L	$I_G = 1.2 I_{GT}$	I - III - IV	MAX.	40	50	mA
		II		80	100	
dV/dt (2)	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	200	400	$\text{V}/\mu\text{s}$
$(dI/dt)_c$ (2)	$(dI/dt)_c = 5.3\text{ A}/\text{ms}$ $T_j = 125^\circ\text{C}$		MIN.	5	10	$\text{V}/\mu\text{s}$

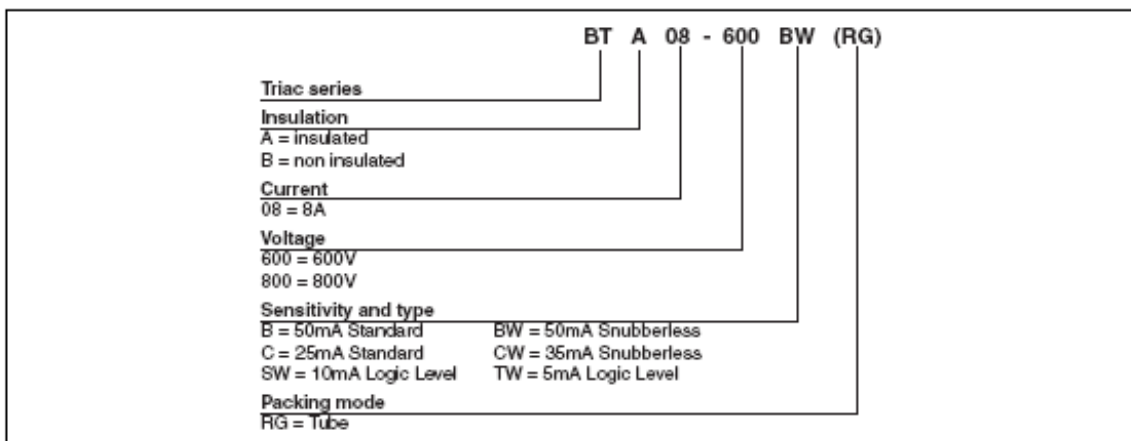
■ 静态特性:

符号	测试条件			数值	单位
V_{TM}	$I_{TM}=11A$, $T_P=380\text{ ms}$	$T_j=25^\circ\text{C}$	MAX	1.55	V
V_{TO}	开启电压	$T_j=125^\circ\text{C}$	MAX	0.85	V
Rd	动态电阻	$T_j=125^\circ\text{C}$	MAX	50	$\text{m}\Omega$
I_{DRM} I_{RRM}	$V_{DRM}=V_{RRM}$	$T_j=25^\circ\text{C}$	MAX	10	μA

■ 热阻:

符号	参数		数值	单位
Rth(j-c)	Junction to case (AC)	TO220AB	1.6	$^\circ\text{C}/\text{W}$
		TO220ABInsulated	2.5	
Rth(j-a)	Junction to ambient	TO220	60	$^\circ\text{C}/\text{W}$
		TO220ABInsulated		

■ 命名方式:



■ 特性曲线:

Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

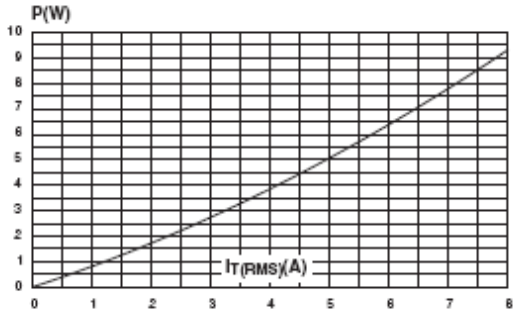


Figure 2: RMS on-state current versus case temperature (full cycle)

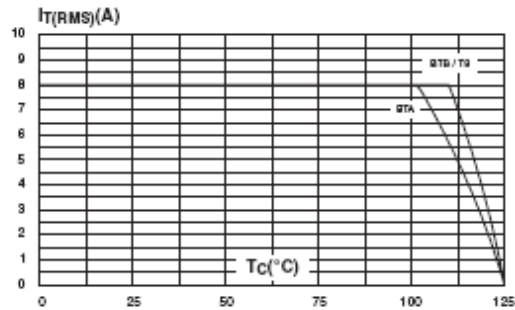


Figure 3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

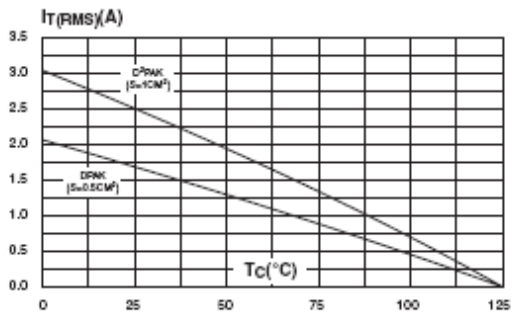


Figure 4: Relative variation of thermal impedance versus pulse duration

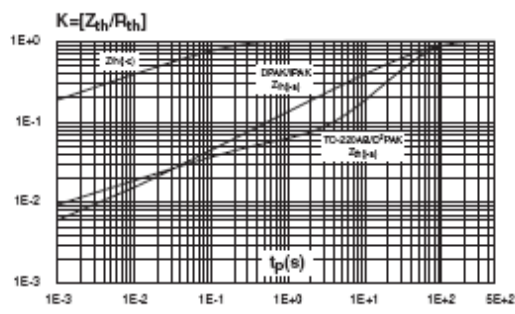


Figure 5: On-state characteristics (maximum values)

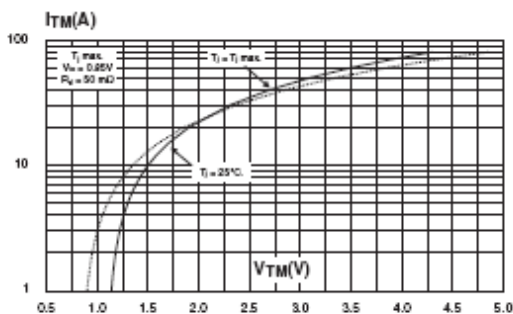
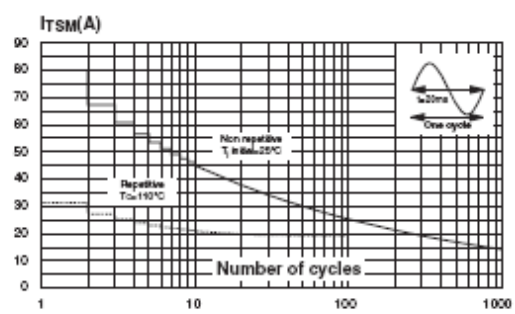


Figure 6: Surge peak on-state current versus number of cycles



■ 特性曲线:

Figure 7: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of I^2t

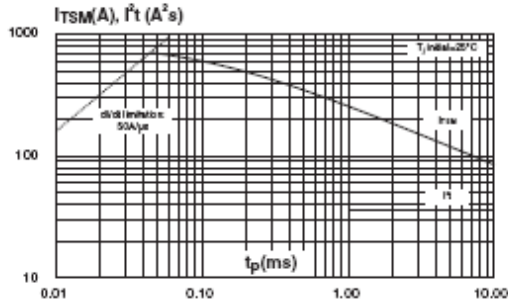


Figure 9: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values) (Snubberless & Logic level types)

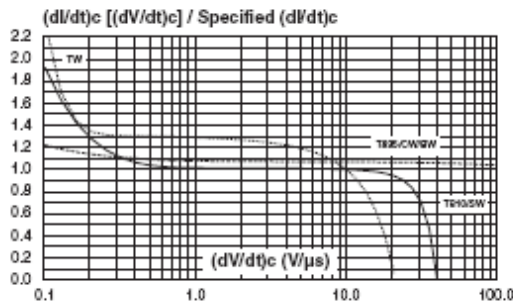


Figure 11: Relative variation of critical rate of decrease of main current versus junction temperature

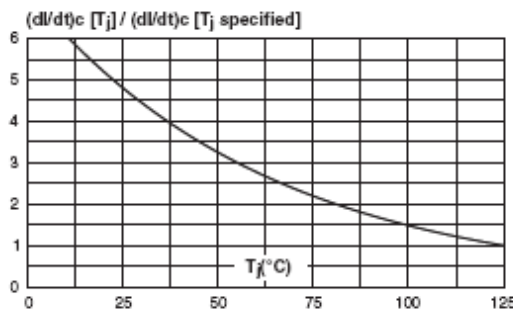


Figure 8: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

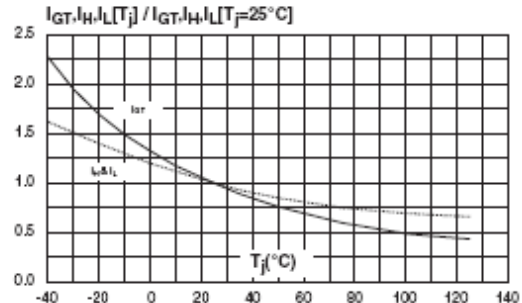


Figure 10: Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values) (Standard types)

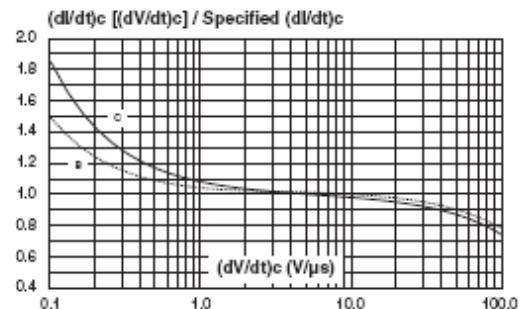
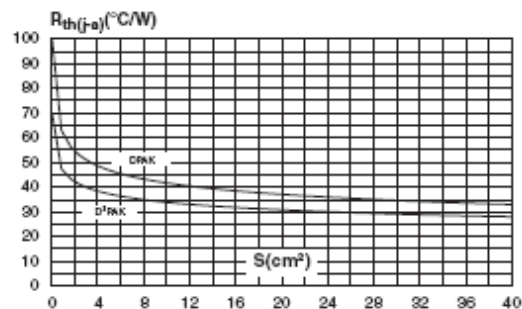


Figure 12: DPAK and D²PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 μm)



■ TO-220AB/TO220ABInsulated 外形尺寸

